

SKN 135F



Stud Diode

Fast Recovery Rectifier Diode

SKN 135F
SKR 135F

Features

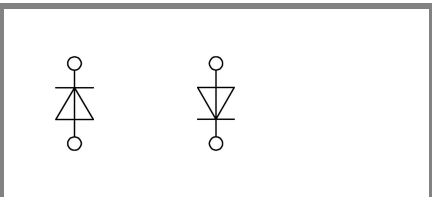
- Small recovered charge
- Soft recovery
- Hermetic metal case with glass insulator
- Threaded stud M12
- SKN: anode to stud;
SKR: cathode to stud

Typical Applications

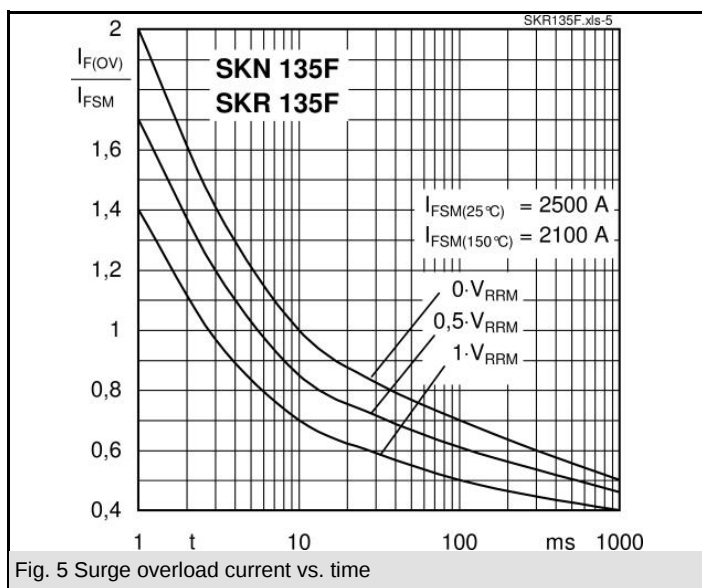
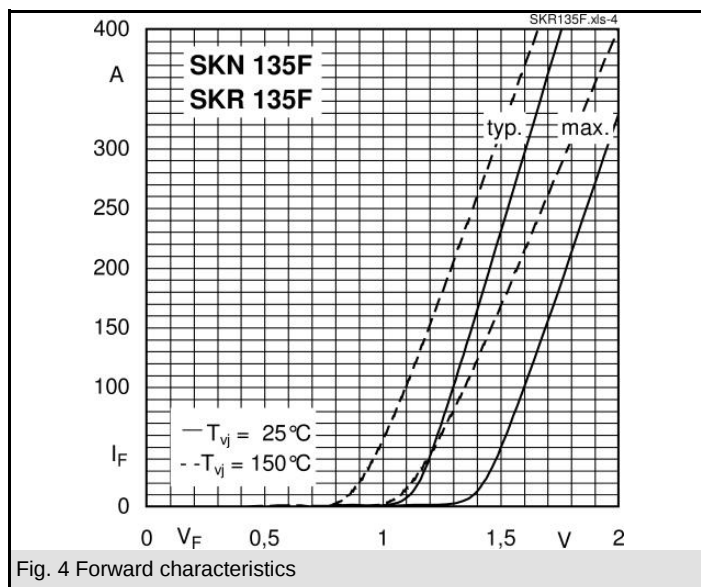
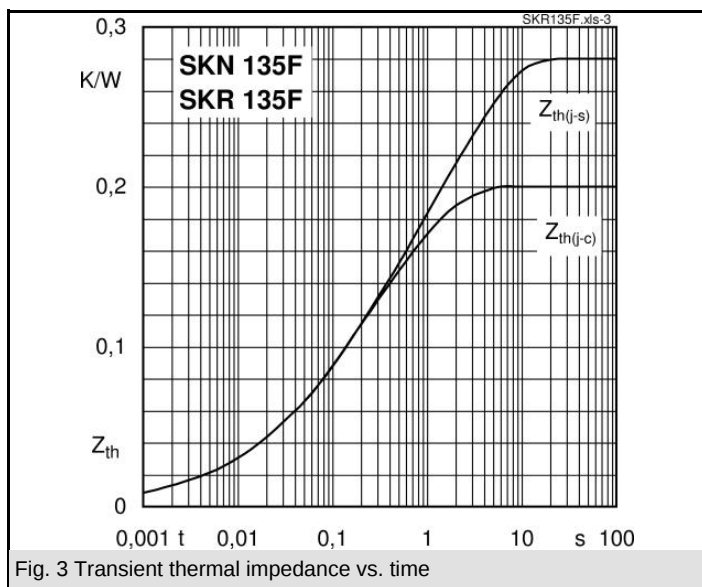
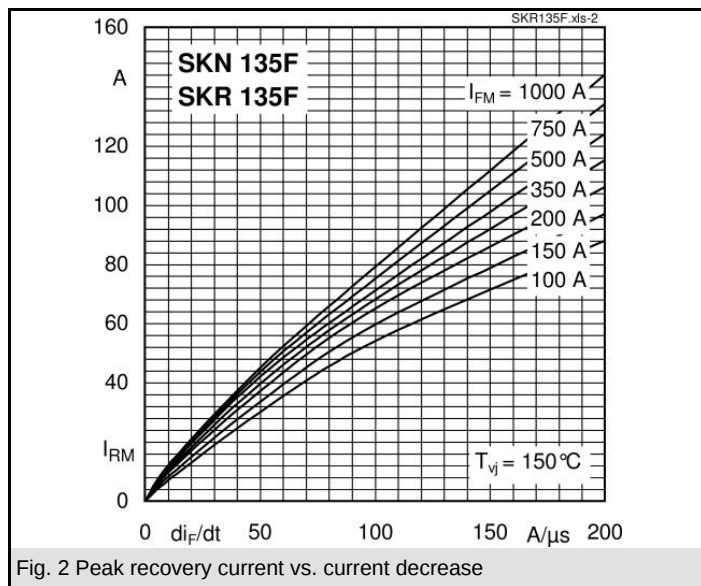
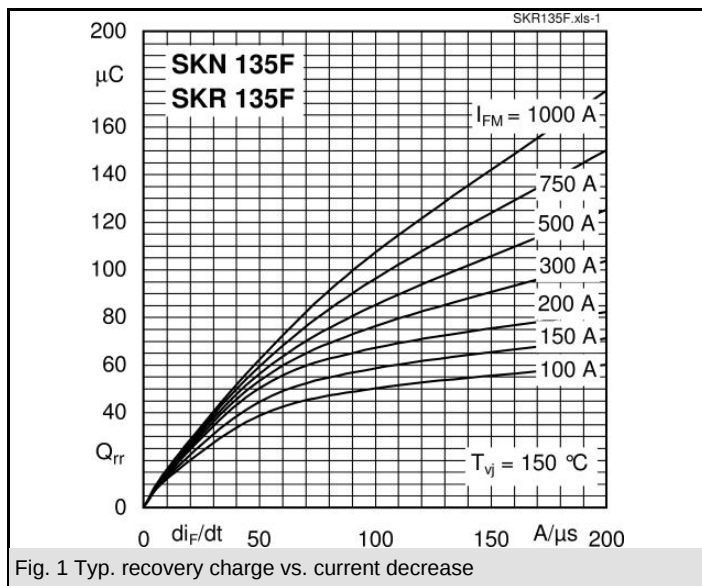
- Inverse diode for GTO and asymmetric thyristor
- Inverters and choppers
- A.C. motor control
- Uninterruptible power supplies (UPS)

V_{RSM} V	V_{RRM} V	$I_{FRMS} = 260\text{ A}$ (maximum value for continuous operation) $I_{FAV} = 135\text{ A}$ (sin. 180; 1000 Hz; $T_c = 100\text{ }^{\circ}\text{C}$)		
800	800	SKN 135F08	SKR 135F08	
1000	1000	SKN 135F10	SKR 135F10	
1200	1200	SKN 135F12	SKR 135F12	

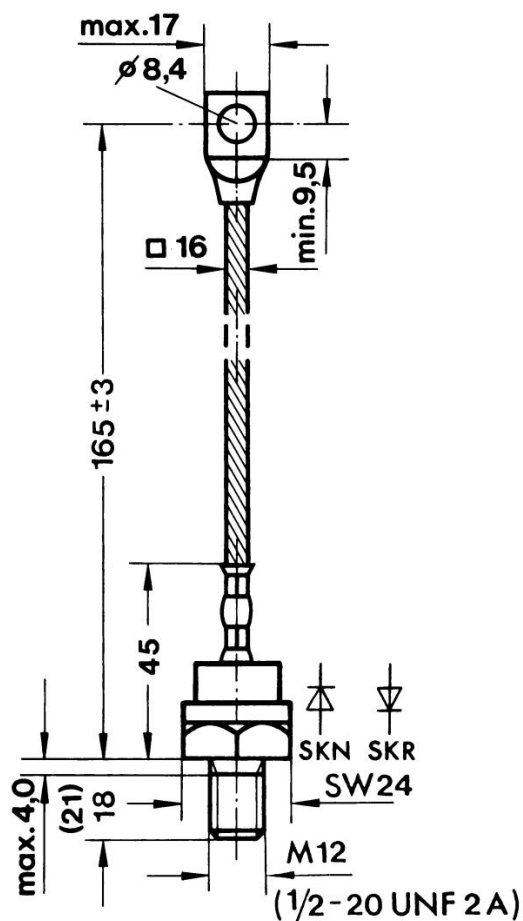
Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_c = 85\text{ (100) }^{\circ}\text{C}$	160 (135)	A
I_{FAV}	K1,1F; $T_a = 35\text{ }^{\circ}\text{C}$; sin. 180; 1000 Hz	110	A
I_{FSM}	$T_{vj} = 25\text{ }^{\circ}\text{C}$; 10 ms	2500	A
	$T_{vj} = 150\text{ }^{\circ}\text{C}$; 10 ms	2100	A
i^2t	$T_{vj} = 25\text{ }^{\circ}\text{C}$; 8,3 ... 10 ms	31000	A ² s
	$T_{vj} = 150\text{ }^{\circ}\text{C}$; 8,3 ... 10 ms	22000	A ² s
V_F	$T_{vj} = 25\text{ }^{\circ}\text{C}$; $I_F = 300\text{ A}$	max. 1,95	V
$V_{(TO)}$	$T_{vj} = 150\text{ }^{\circ}\text{C}$	max. 1,1	V
r_T	$T_{vj} = 150\text{ }^{\circ}\text{C}$	max. 2,3	mΩ
I_{RD}	$T_{vj} = 25\text{ }^{\circ}\text{C}$; $V_{RD} = V_{RRM}$	max. 1	mA
I_{RD}	$T_{vj} = 150\text{ }^{\circ}\text{C}$; $V_{RD} = V_{RRM}$	max. 100	mA
Q_{rr}	$T_{vj} = 150\text{ }^{\circ}\text{C}$; $I_F = 100\text{ A}$,	50	μC
I_{RM}	$-di/dt = 100\text{ A/}\mu\text{s}$, $V_R = 400\text{ V}$	53	A
t_{rr}		1900	ns
E_{rr}		-	mJ
$R_{th(j-c)}$		0,2	K/W
$R_{th(c-s)}$		0,08	K/W
T_{vj}		- 40 ... + 150	°C
T_{stg}		- 55 ... + 150	°C
V_{isol}		-	V~
M_s	to heatsink	10	Nm
a		5 * 9,81	m/s ²
m	approx.	100	g
Case	135F	E 14	



SKN SKR



Dimensions in mm



Case E 14 (IEC 60191: A 9 MA modified; JEDEC: DO-205 AC (DO-30) modified)

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